

Description

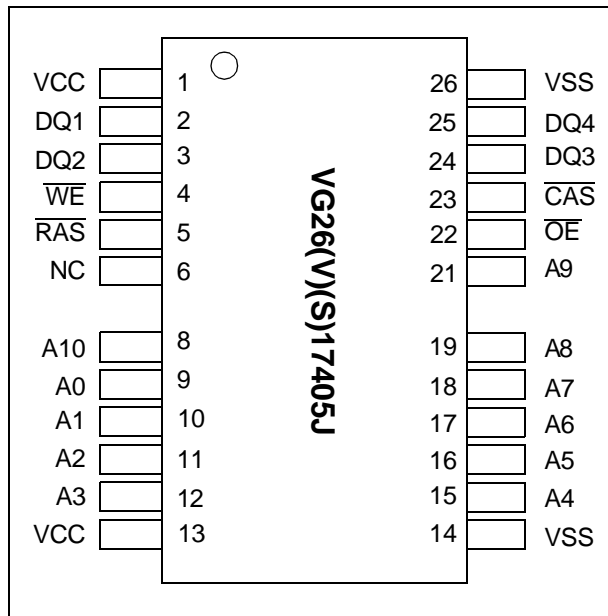
The device CMOS Dynamic RAM organized as 4,194,304 words x 4 bits with extended data out access mode. It is fabricated with an advanced submicron CMOS technology and designed to operate from a single 5V only or 3.3V only power supply. Low voltage operation is more suitable to be used on battery backup, portable electronic application. Self-Refresh is supported and CBR cycles are being performed. It is packaged in JEDEC standard 26/24-pin plastic SOJ or TSOPII.

Features

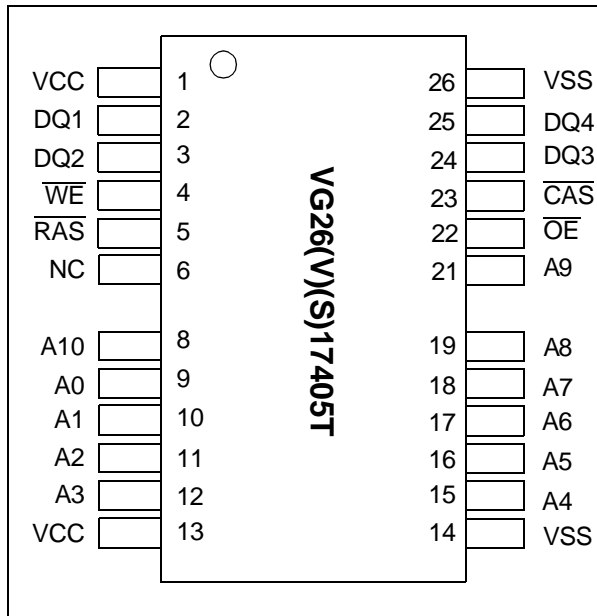
- Single 5V($\pm 10\%$) or 3.3V(3.15V~3.6V) only power supply
- High speed t_{RAC} access time: 50/60ns
- Extended - data - out(EDO) page mode access
- I/O level: TTL compatible ($V_{cc} = 5V$)
 LVTTL compatible ($V_{cc} = 3.3V$)
- 4 refresh modes:
 - \overline{RAS} only refresh
 - \overline{CAS} - before - \overline{RAS} refresh
 - Hidden refresh
 - Self-refresh
- Refresh interval:
 - \overline{RAS} only refresh, \overline{CAS} - before - \overline{RAS} refresh and hidden refresh: 2048 cycles in 32ms
 - Self-refresh: 2048 cycles
- JEDEC standard pinout: 26/24-pin plastic SOJ and TSOPII.

Pin Configuration

26/24-PIN 300mil Plastic SOJ



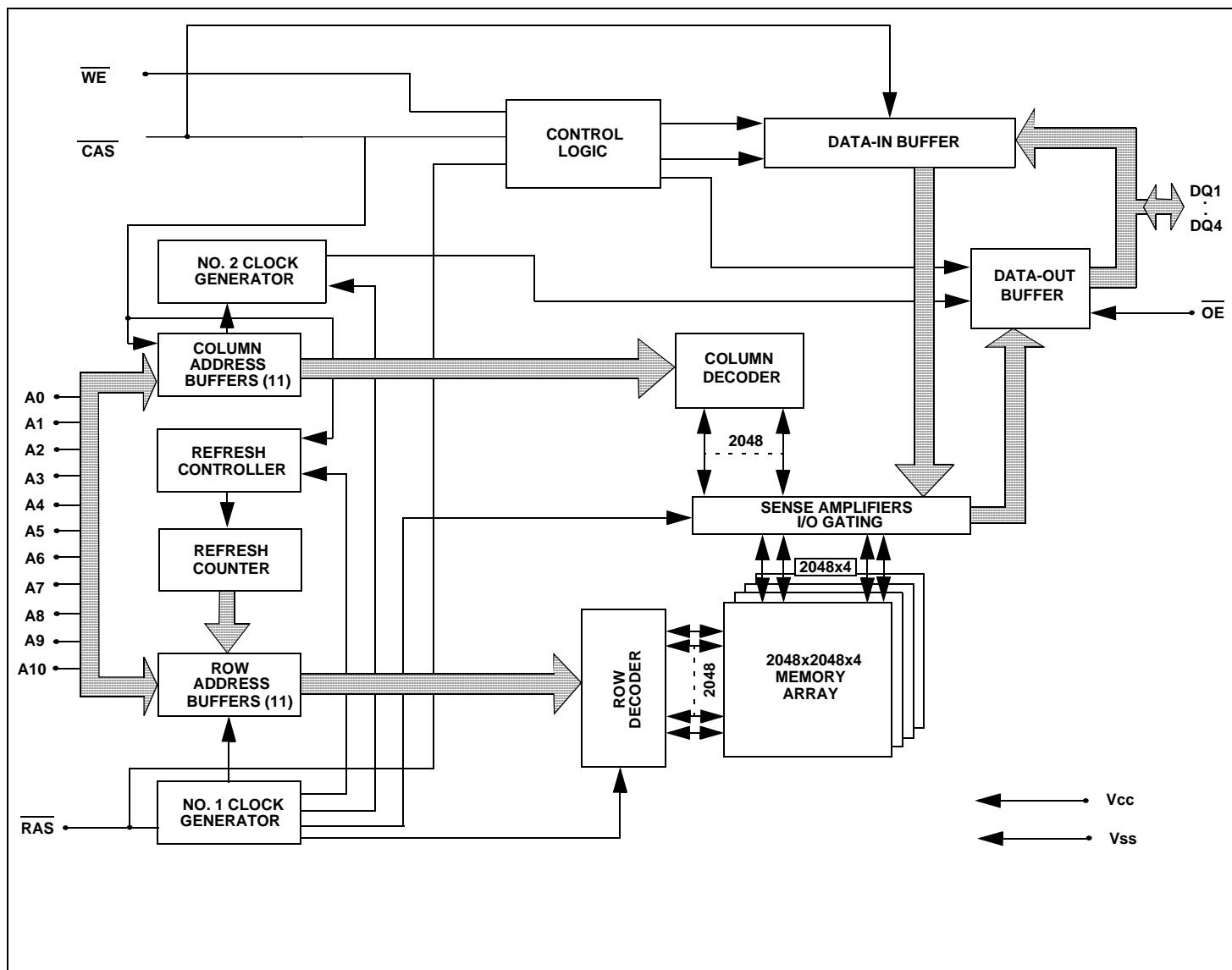
26/24-PIN 300mil Plastic TSOP (II)



Pin Description

Pin Name	Function
A0-A10	Address inputs - Row address A0-A10 - Column address A0-A10 - Refresh address A0-A10
DQ1~DQ4	Data-in / data-out
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{CAS}}$	Column address strobe
$\overline{\text{WE}}$	Write enable
$\overline{\text{OE}}$	Output enable
Vcc	Power (+5 V or + 3.3V)
Vss	Ground

Block Diagram



TRUTH TABLE

FUNCTION		$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	ADDRESSES		DQ _S	Notes
						ROW	COL		
STANDBY		H	H → X	X	X	X	X	High-Z	
READ		L	L	H	L	ROW	COL	Data-Out	
WRITE: (EARLY WRITE)		L	L	L	X	ROW	COL	Data-In	
READ WRITE		L	L	H → L	L → H	ROW	COL	Data-Out, Data-In	
EDO-PAGE-MODE READ	1st Cycle	L	H → L	H	L	ROW	COL	Data-Out	
	2nd Cycle	L	H → L	H	L	n/a	COL	Data-Out	
EDO-PAGE-MODE WRITE	1st Cycle	L	H → L	L	X	ROW	COL	Data-In	
	2nd Cycle	L	H → L	L	X	n/a	COL	Data-In	
EDO-PAGE-MODE READ-WRITE	1st Cycle	L	H → L	H → L	L → H	ROW	COL	Data-Out, Data-In	
	2nd Cycle	L	H → L	H → L	L → H	n/a	COL	Data-Out, Data-In	
HIDDEN REFRESH	READ	L → H → L	L	H	L	ROW	COL	Data-Out	
	WRITE	L → H → L	L	L	X	ROW	COL	Data-In	1
RAS-ONLY REFRESH		L	H	X	X	ROW	n/a	High-Z	
CBR REFRESH		H → L	L	H	X	X	X	High-Z	

Notes: 1. EARLY WRITE only.

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to Vss	V_T	5V -1.0 to + 7.0	V
3.3V		-0.5 to + 4.6	
Supply voltage relative to Vss	V_{CC}	5V -1.0 to + 7.0	V
3.3V		-0.5 to + 4.6	
Short circuit output current	I_{OUT}	50	mA
Power dissipation	P_D	1.0	W
Operating temperature	T_{OPT}	0 to + 70	°C
Storage temperature	T_{STG}	-55 to + 125	°C

Recommended DC Operating Conditions

Parameter/Condition	Symbol	5 Volt Version			3.3 Volt Version			Unit
		Min	Typ	Max	Min	Typ	Max	
Supply Voltage	V_{CC}	4.5	5.0	5.5	3.15	3.3	3.6	V
Input High Voltage, all inputs	V_{IH}	2.4	-	$V_{CC} + 1.0$	2.0	-	$V_{CC} + 0.3$	V
Input Low Voltage, all inputs	V_{IL}	-1.0	-	0.8	-0.3	-	0.8	V

Capacitance

Ta = 25°C, V_{CC} = 5V or 3.3V, f = 1MHz

Parameter	Symbol	Typ	Max	Unit	Note
Input capacitance (Address)	C_{I1}	-	5	pF	1
Input capacitance (\overline{RAS} , \overline{CAS} , \overline{OE} , \overline{WE})	C_{I2}	-	7	pF	1
Output capacitance (Data-in, Data-out)	$C_{I/O}$	-	7	pF	1, 2

Note: 1. Capacitance measured with effective capacitance measuring method.

2. \overline{RAS} , \overline{CAS} = V_{IH} to disable Dout.

DC Characteristics; 5- Volt Verion

($T_a = 0$ to $+70$ °C, $V_{CC} = +5V \pm 10\%$, $V_{SS} = 0V$)

Parameter	Symbol	Test Conditions	VG26(V)(S)17405				Unit	Notes
			-5		-6			
			Min	Max	Min	Max		
Operating current	I _{CC1}	\overline{RAS} cycling CAS cycling t _{RC} = min	-	120	-	110	mA	1, 2
Standby Current	I _{CC2}	TTL interface RAS, CAS = V _{IH} Dout = High-Z	-	2	-	2	mA	
		CMOS interface \overline{RAS} , $\overline{CAS} \geq V_{CC} - 0.2V$ Dout = High-Z		1	-	1	mA	
\overline{RAS} -only refresh current	I _{CC3}	\overline{RAS} cycling, $\overline{CAS} = V_{IH}$ t _{RC} = min	-	120	-	110	mA	1, 2
EDO page mode current	I _{CC4}	t _{PC} = min	-	140	-	130	mA	1, 3
\overline{CAS} -before- \overline{RAS} refresh current	I _{CC5}	t _{RC} = min \overline{RAS} , \overline{CAS} cycling	-	120	-	110	mA	1, 2
Self-refresh current	I _{CC8}	t _{RAS} ≥ 100μs		600		600	μA	4
		t _{RAS} ≥ 100μs (low power ver- sion)	-	350	-	350	μA	5

Notes:

1. I_{CC} is specified as an average current. It depends on output loading condition and cycle rate when the device is selected. I_{CC} max is specified at the output open condition.
2. Address can be changed once or less while $\overline{RAS} = V_{IL}$.
3. For I_{CC4} , address can be changed once or less within one EDO page mode cycle time.
4. Normal version: VG26S17405FT, VG26S17405FJ
5. Low power version: VG26S17405FTL, VG26S17405FJL

DC Characteristics ; 5-Volt Version (Cont.)

($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = +5\text{V} \pm 10\%$, $V_{SS} = 0\text{V}$)

Parameter	Symbol	Test Conditions	VG26(V)(S)17405				Unit	Notes
			-5		-6			
			Min	Max	Min	Max		
Input leakage current	I _{LI}	0V ≤ V _{IN} ≤ V _{CC} + 0.5V	-5	5	-5	5	μA	
Output leakage current	I _{LO}	0V ≤ V _{OUT} ≤ V _{CC} + 0.5V Dout = Disable	-5	5	-5	5	μA	
Output high Voltage	V _{OH}	I _{OH} = - 5mA	2.4	-	2.4	-	V	
Output low voltage	V _{OL}	I _{OL} = + 4.2mA	-	0.4	-	0.4	V	

DC Characteristics ; 3.3 - Volt Version

($T_a = 0$ to 70°C , $V_{CC} = +3.3\text{V}(3.15\text{V}\sim 3.6\text{V})$, $V_{SS} = 0\text{V}$)

Parameter	Symbol	Test Conditions	VG26(V)(S)17405				Unit	Notes
			-5		-6			
			Min	Max	Min	Max		
Operating current	I _{CC1}	$\overline{\text{RAS}}$ cycling CAS cycling t _{RC} = min	-	120	-	110	mA	1, 2
Standby Current	I _{CC2}	LVTTL interface RAS, CAS = V _{IH} Dout = High-Z	-	2	-	2	mA	
		CMOS interface $\overline{\text{RAS}}, \overline{\text{CAS}} \geq V_{\text{CC}} - 0.2\text{V}$ Dout = High-Z	-	0.5	-	0.5	mA	
$\overline{\text{RAS}}$ - only refresh current	I _{CC3}	$\overline{\text{RAS}}$ cycling, $\overline{\text{CAS}} = V_{\text{IH}}$ t _{RC} = min	-	120	-	110	mA	1, 2
EDO page mode current	I _{CC4}	t _{PC} = min	-	90	-	80	mA	1, 3
$\overline{\text{CAS}}$ - before- $\overline{\text{RAS}}$ refresh current	I _{CC5}	t _{RC} = min RAS, CAS cycling	-	120	-	110	mA	1, 2
Self- refresh current	I _{CC8}	t _{RAS} ≥ 100μs		550		550	μA	4
		t _{RAS} ≥ 100μs (low power version)	-	350	-	350	μA	5

Notes:

- I_{CC} is specified as an average current. It depends on output loading condition and cycle rate when the device is selected. I_{CC} max is specified at the output open condition.
- Address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$.
- For I_{CC4} , address can be changed once or less within one EDO page mode cycle time.
- Normal version: VG26VS17405FT, VG26VS17405FJ
- Low power version: VG26VS17405FTL, VG26VS17405FJL

DC Characteristics ; 3.3 - Volt Version (Cont.)

($T_a = 0$ to 70°C , $V_{CC} = +3.3\text{V}$ (3.15V~3.6V), $V_{SS} = 0\text{V}$)

Parameter	Symbol	Test Conditions	VG26(V)(S)17405				Unit	Notes
			-5		-6			
			Min	Max	Min	Max		
Input leakage current	I _{LI}	0V ≤ Vin ≤ V _{CC} + 0.3V	-5	5	-5	5	μA	
Output leakage current	I _{LO}	0V ≤ Vout ≤ V _{CC} + 0.3V Dout = Disable	-5	5	-5	5	μA	
Output high Voltage	V _{OH}	I _{OH} = -2mA	2.4	-	2.4	-	V	
Output low voltage	V _{OL}	I _{OL} = +2mA	-	0.4	-	0.4	V	

AC Characteristics

($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{V}$ or 3.3V , $V_{SS} = 0\text{V}$) *1, *2, *3, *4

Test conditions

- Output load: two TTL Loads and 100pF ($V_{CC} = 5.0\text{V} \pm 10\%$)
one TTL Load and 100pF ($V_{CC} = 3.3\text{V}(3.15\text{V} \sim 3.6\text{V})$)
- Input timing reference levels:
 $V_{IH} = 2.4\text{V}$, $V_{IL} = 0.8\text{V}$ ($V_{CC} = 5.0\text{V} \pm 10\%$); $V_{IH} = 2.0\text{V}$, $V_{IL} = 0.8\text{V}$ ($V_{CC} = 3.3\text{V}(3.15\text{V} \sim 3.6\text{V})$)
- Output timing reference levels:
 $V_{OH} = 2.0\text{V}$, $V_{OL} = 0.8\text{V}$ ($V_{CC} = 5\text{V} \pm 10\%$, $3.3\text{V}(3.15\text{V} \sim 3.6\text{V})$)

Read, Write, Read- Modify- Write and Refresh Cycles

(Common Parameters)

Parameter	Symbol	VG26(V)(S) 17405				Unit	Notes
		-5		-6			
		Min	Max	Min	Max		
Random read or write cycle time	t _{RC}	84	-	104	-	ns	
RAS precharge time	t _{RP}	30	-	40	-	ns	
CAS precharge time in normal mode	t _{CPN}	10	-	10	-	ns	
RAS pulse width	t _{RAS}	50	10000	60	10000	ns	5
CAS pulse width	t _{CAS}	8	10000	10	10000	ns	6
Row address setup time	t _{ASR}	0	-	0	-	ns	
Row address hold time	t _{RAH}	8	-	10	-	ns	
Column address setup time	t _{ASC}	0	-	0	-	ns	7
Column address hold time	t _{CAH}	8	-	10	-	ns	
RAS to CAS delay time	t _{RCD}	12	37	14	45	ns	8
RAS to column address delay time	t _{RAD}	10	25	12	30	ns	9
Column address to RAS lead time	t _{RAL}	25	-	30	-	ns	
RAS hold time	t _{RSH}	8	-	10	-	ns	
CAS hold time	t _{CSH}	38	-	40	-	ns	
CAS to RAS precharge time	t _{CRP}	5	-	5	-	ns	10
OE to Din delay time	t _{OED}	20	-	20	-	ns	
Transition time (rise and fall)	t _T	1	50	1	50	ns	11
Refresh period	t _{REF}	-	32	-	32	ms	
CAS to output in Low- Z	t _{CLZ}	0	-	0	-	ns	
CAS delay time from Din	t _{DZC}	0	-	0	-	ns	
OE delay time from Din	t _{DZO}	0	-	0	-	ns	

Read Cycle

Parameter	Symbol	VG26(V)(S)17405				Unit	Notes
		-5		-6			
		Min	Max	Min	Max		
Access time from $\overline{\text{RAS}}$	t_{RAC}	-	50	-	60	ns	12
Access time from $\overline{\text{CAS}}$	t_{CAC}	-	14	-	15	ns	13, 14
Access time from column address	t_{AA}	-	25	-	30	ns	14, 15
Access time from $\overline{\text{OE}}$	t_{OEA}	-	12	-	15	ns	
Read command setup time	t_{RCS}	0	-	0	-	ns	7
Read command hold time to $\overline{\text{CAS}}$	t_{RCH}	0	-	0	-	ns	10, 16
Read command hold time to $\overline{\text{RAS}}$	t_{RRH}	0	-	0	-	ns	16
Output buffer turn-off time	t_{OFF}	0	12	0	15	ns	17
Output buffer turn-off time from $\overline{\text{OE}}$	t_{OEZ}	0	12	0	15	ns	17

Write Cycle

Parameter	Symbol	VG26(V)(S)17405				Unit	Notes
		-5		-6			
		Min	Max	Min	Max		
Write command setup time	t _{WCS}	0	-	0	-	ns	7, 18
Write command hold time	t _{WCH}	8	-	10	-	ns	
Write command pulse width	t _{WP}	8	-	10	-	ns	
Write command to $\overline{\text{RAS}}$ lead time	t _{RWL}	13	-	15	-	ns	
Write command to $\overline{\text{CAS}}$ lead time	t _{CWL}	8	-	10	-	ns	
Data-in setup time	t _{DS}	0	-	0	-	ns	19
Data-in hold time	t _{DH}	8	-	10	-	ns	19
$\overline{\text{WE}}$ to Data-in delay	t _{WED}	10	-	10	-	ns	

Read- Modify- Write Cycle

Parameter	Symbol	VG26(V)(S) 17405				Unit	Notes
		-5		-6			
		Min	Max	Min	Max		
Read-modify- write cycle time	t _{RWC}	108	-	133	-	ns	
$\overline{\text{RAS}}$ to $\overline{\text{WE}}$ delay time	t _{RWD}	64	-	77	-	ns	18
$\overline{\text{CAS}}$ to $\overline{\text{WE}}$ dealy time	t _{CWD}	26	-	32	-	ns	18
Column address to $\overline{\text{WE}}$ delay time	t _{AWD}	39	-	47	-	ns	18
$\overline{\text{OE}}$ hold time from $\overline{\text{WE}}$	t _{OEH}	8	-	10	-	ns	

Refresh Cycle

Parameter	Symbol	VG26(V)(S)17405				Unit	Notes
		-5		-6			
		Min	Max	Min	Max		
CAS setup time (CBR refresh)	t _{CSR}	5	-	5	-	ns	
CAS hold time (CBR refresh)	t _{CHR}	8	-	10	-	ns	10
RAS precharge to CAS hold time	t _{RPC}	5	-	5	-	ns	7
RAS pulse width (self refresh)	t _{RASS}	100	-	100	-	μs	
RAS precharge time (self refresh)	t _{RPS}	90	-	110	-	ns	
CAS hold time (CBR self refresh)	t _{CHS}	-50	-	-50	-	ns	
WE setup time	t _{WSR}	0	-	0	-	ns	
WE hold time	t _{WHR}	10	-	10	-	ns	

EDO Page Mode Cycle

Parameter	Symbol	VG26(V)(S) 17405				Unit	Notes
		-5		-6			
		Min	Max	Min	Max		
EDO page mode cycle time	t _{PC}	20	-	25	-	ns	
EDO page mode $\overline{\text{CAS}}$ precharge time	t _{CP}	10	-	10	-	ns	
EDO page mode $\overline{\text{RAS}}$ pulse width	t _{RASP}	50	10 ⁵	60	10 ⁵	ns	20
Access time from $\overline{\text{CAS}}$ precharge	t _{CPA}	-	30	-	35	ns	10, 14
$\overline{\text{RAS}}$ hold time from $\overline{\text{CAS}}$ precharge	t _{CPRH}	30	-	35	-	ns	
$\overline{\text{OE}}$ high hold time from $\overline{\text{CAS}}$ high	t _{OEHC}	5	-	5	-	ns	
$\overline{\text{OE}}$ high pulse width	t _{OEP}	10	-	10	-	ns	
Data output hold time after $\overline{\text{CAS}}$ low	t _{COH}	5	-	5	-	ns	
Output disable delay from $\overline{\text{WE}}$	t _{WHZ}	3	10	3	10	ns	
$\overline{\text{WE}}$ pulse width for output disable when $\overline{\text{CAS}}$ high	t _{WPZ}	10	-	10	-	ns	

EDO Page Mode Read Modify Write Cycle

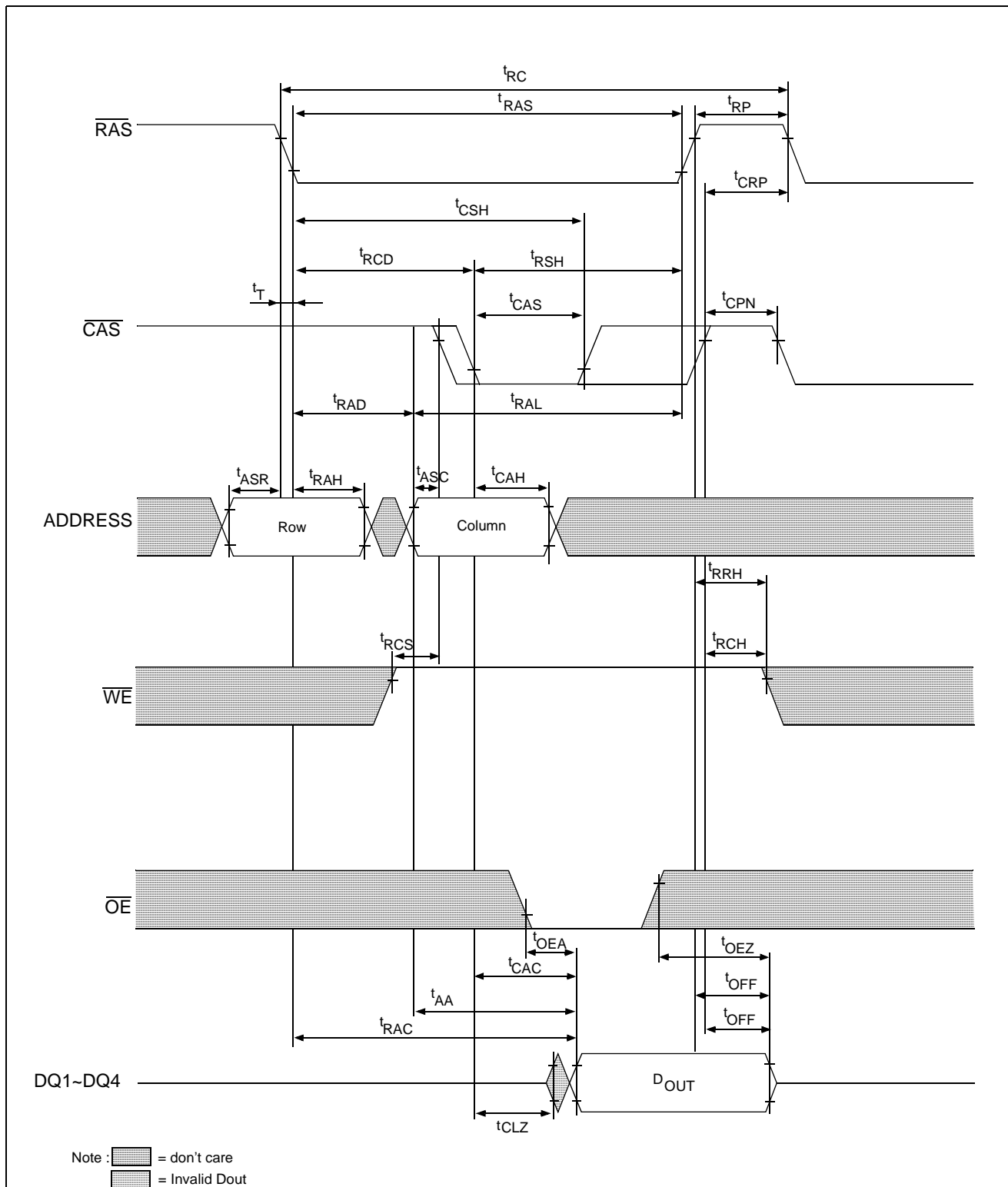
Parameter	Symbol	VG26(V)(S)17405				Unit	Notes
		-5		-6			
		Min	Max	Min	Max		
EDO page mode read- modify- write cycle CAS precharge to WE delay time	t _{CPW}	45	-	55	-	ns	10
EDO page mode read- modify- write cycle time	t _{PRWC}	56	-	68	-	ns	

Notes :

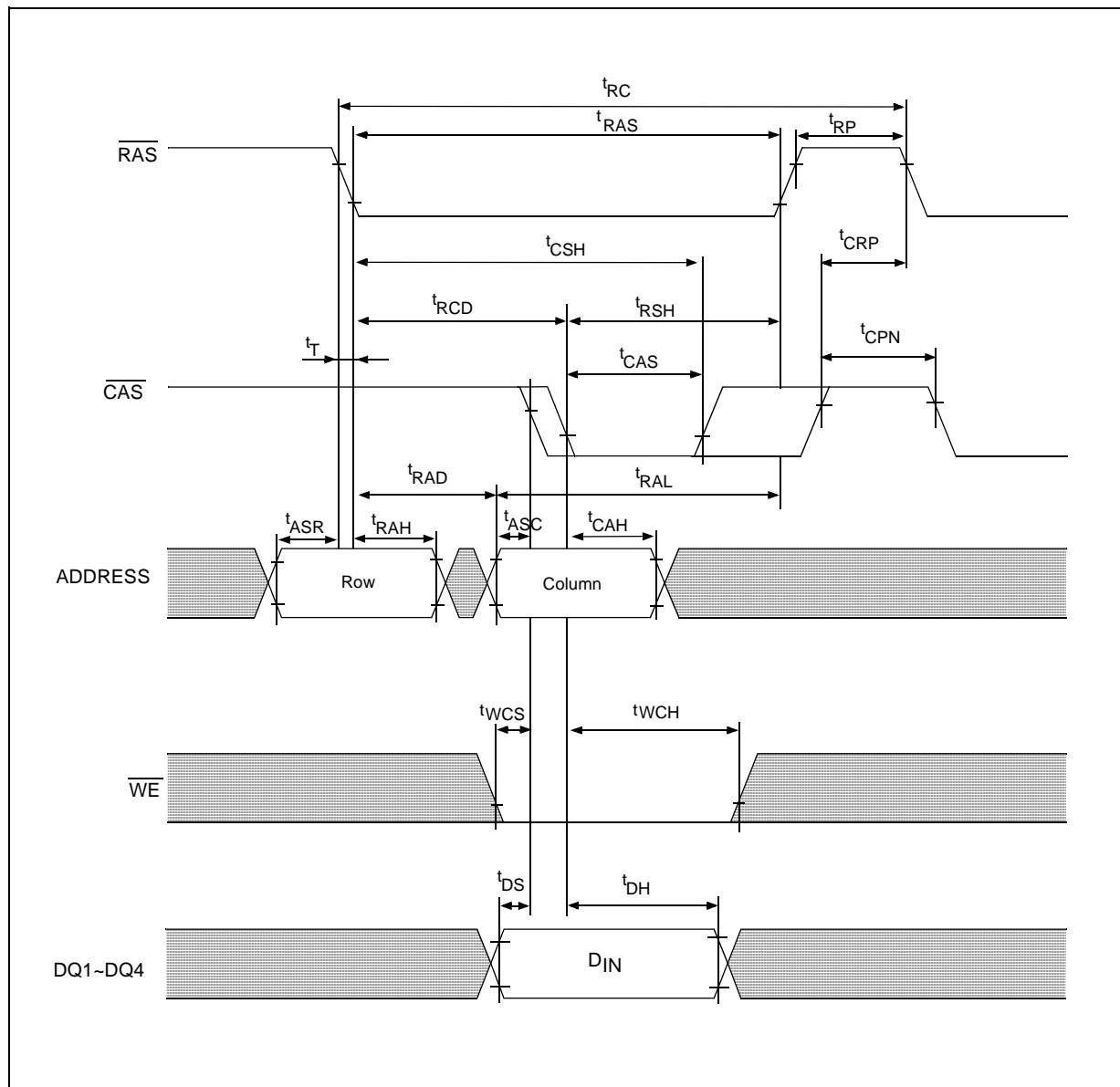
1. AC measurements assume $t_T = 1\text{ns}$.
2. An initial pause of $100\ \mu\text{s}$ is required after power up, and it is followed by a minimum of eight initialization cycles ($\overline{\text{RAS}}$ - only refresh cycle or $\overline{\text{CAS}}$ - before - $\overline{\text{RAS}}$ refresh cycle). If the internal refresh counter is used, a minimum of eight $\overline{\text{CAS}}$ - before - $\overline{\text{RAS}}$ refresh cycles are required.
3. In delayed write or read-modify-write cycles, $\overline{\text{OE}}$ must disable output buffer prior to applying data to the device.
4. All the V_{CC} and V_{SS} pins shall be supplied with the same voltages.
5. $t_{\text{RAS}}(\text{min}) = t_{\text{RWD}}(\text{min}) + t_{\text{RWL}}(\text{min}) + t_T$ in read-modify-write cycle.
6. $t_{\text{CAS}}(\text{min}) = t_{\text{CWD}}(\text{min}) + t_{\text{CWL}}(\text{min}) + t_T$ in read-modify-write cycle.
7. $t_{\text{ASC}}(\text{min})$, $t_{\text{RCS}}(\text{min})$, $t_{\text{WCS}}(\text{min})$, and t_{RPC} are determined by the falling edge of $\overline{\text{CAS}}$.
8. $t_{\text{RCD}}(\text{max})$ is specified as a reference point only, and $t_{\text{RAC}}(\text{max})$ can be met with the $t_{\text{RCD}}(\text{max})$ limit. Otherwise, t_{RAC} is controlled exclusively by t_{CAC} if t_{RCD} is greater than the specified $t_{\text{RCD}}(\text{max})$ limit.
9. $t_{\text{RAD}}(\text{max})$ is specified as a reference point only, and $t_{\text{RAC}}(\text{max})$ can be met with the $t_{\text{RAD}}(\text{max})$ limit. Otherwise, t_{RAC} is controlled exclusively by t_{AA} if t_{RAD} is greater than the specified $t_{\text{RAD}}(\text{max})$ limit.
10. t_{CRP} , t_{CHR} , t_{RCH} , t_{CPA} and t_{CPW} are determined by the rising edge of $\overline{\text{CAS}}$.
11. $V_{\text{IH}}(\text{min})$ and $V_{\text{IL}}(\text{max})$ are reference levels for measuring timing or input signals. Therefore, transition time is measured between V_{IH} and V_{IL} .
12. Assumes that $t_{\text{RCD}} \leq t_{\text{RCD}}(\text{max})$ and $t_{\text{RAD}} \leq t_{\text{RAD}}(\text{max})$. If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
13. Assumes that $t_{\text{RCD}} \geq t_{\text{RCD}}(\text{max})$ and $t_{\text{RAD}} \leq t_{\text{RAD}}(\text{max})$.
14. Access time is determined by the maximum of t_{AA} , t_{CAC} , t_{CPA} .
15. Assumes that $t_{\text{RCD}} \leq t_{\text{RCD}}(\text{max})$ and $t_{\text{RAD}} \geq t_{\text{RAD}}(\text{max})$.
16. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
17. $t_{\text{OFF}}(\text{max})$ and $t_{\text{OEZ}}(\text{max})$ define the time at which the output achieves the open circuit condition (high impedance). t_{OFF} is determined by the later rising edge of $\overline{\text{RAS}}$ or $\overline{\text{CAS}}$.
18. t_{WCS} , t_{RWD} , t_{CWD} , and t_{AWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{\text{WCS}} \geq t_{\text{WCS}}(\text{min})$, the cycle is an early write cycle and the data out will remain open circuit (high impedance) throughout the entire cycle. If $t_{\text{RWD}} \geq t_{\text{RWD}}(\text{min})$, $t_{\text{CWD}} \geq t_{\text{CWD}}(\text{min})$, $t_{\text{AWD}} \geq t_{\text{AWD}}(\text{min})$ and $t_{\text{CPW}} \geq t_{\text{CPW}}(\text{min})$, the cycle is a read-modify-write and the data output will contain data read from the selected cell. If neither of the above sets of conditions is satisfied, the condition of the data output (at access time) is indeterminate.
19. These parameters are referenced to $\overline{\text{CAS}}$ separately in an early write cycle and to $\overline{\text{WE}}$ edge in a delayed write or a read-modify-write cycle.
20. t_{RASP} defines $\overline{\text{RAS}}$ pulse width in EDO page mode cycles.

Timing Waveforms

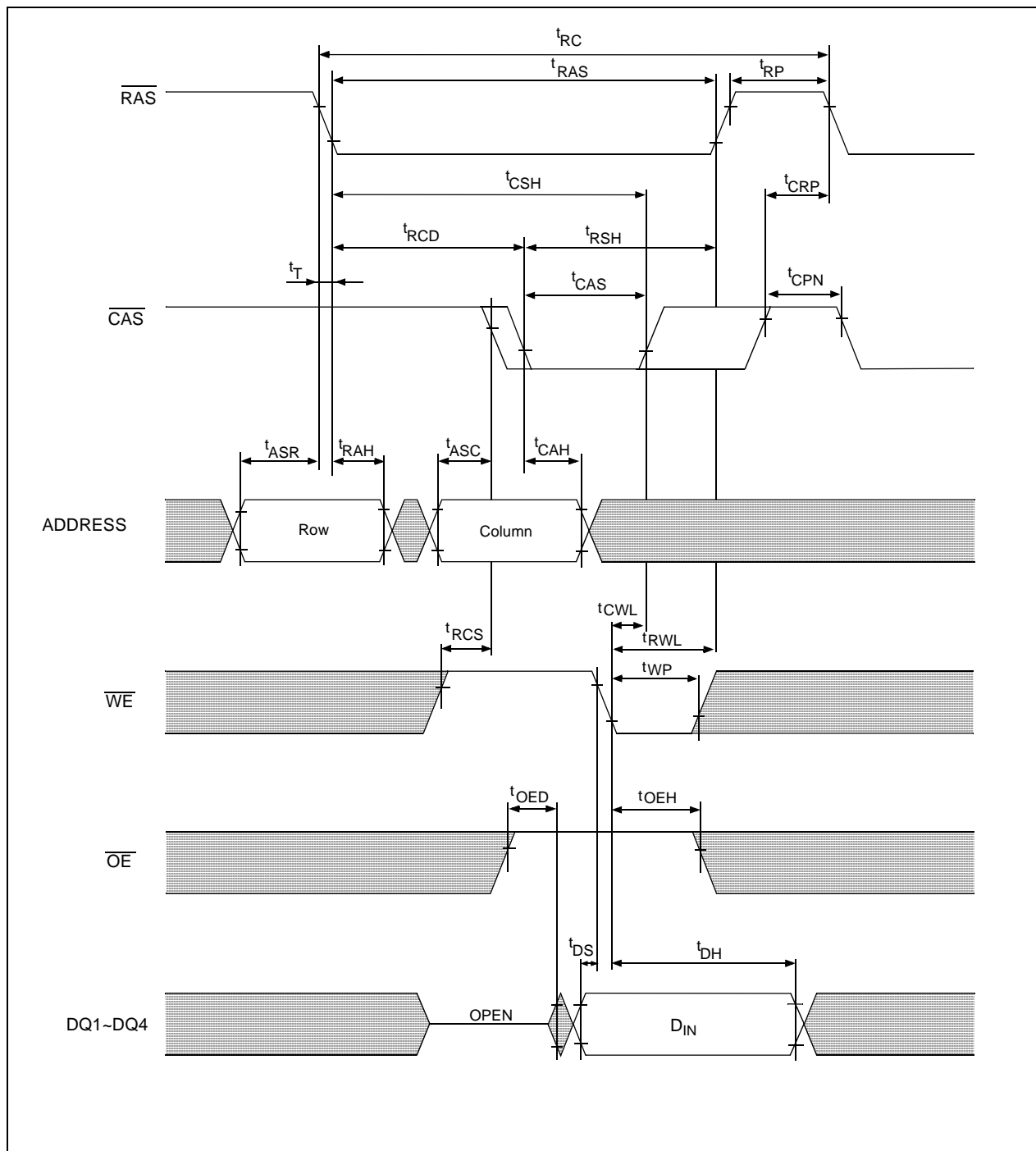
• Read Cycle



•Early Write Cycle



• Delayed Write Cycle

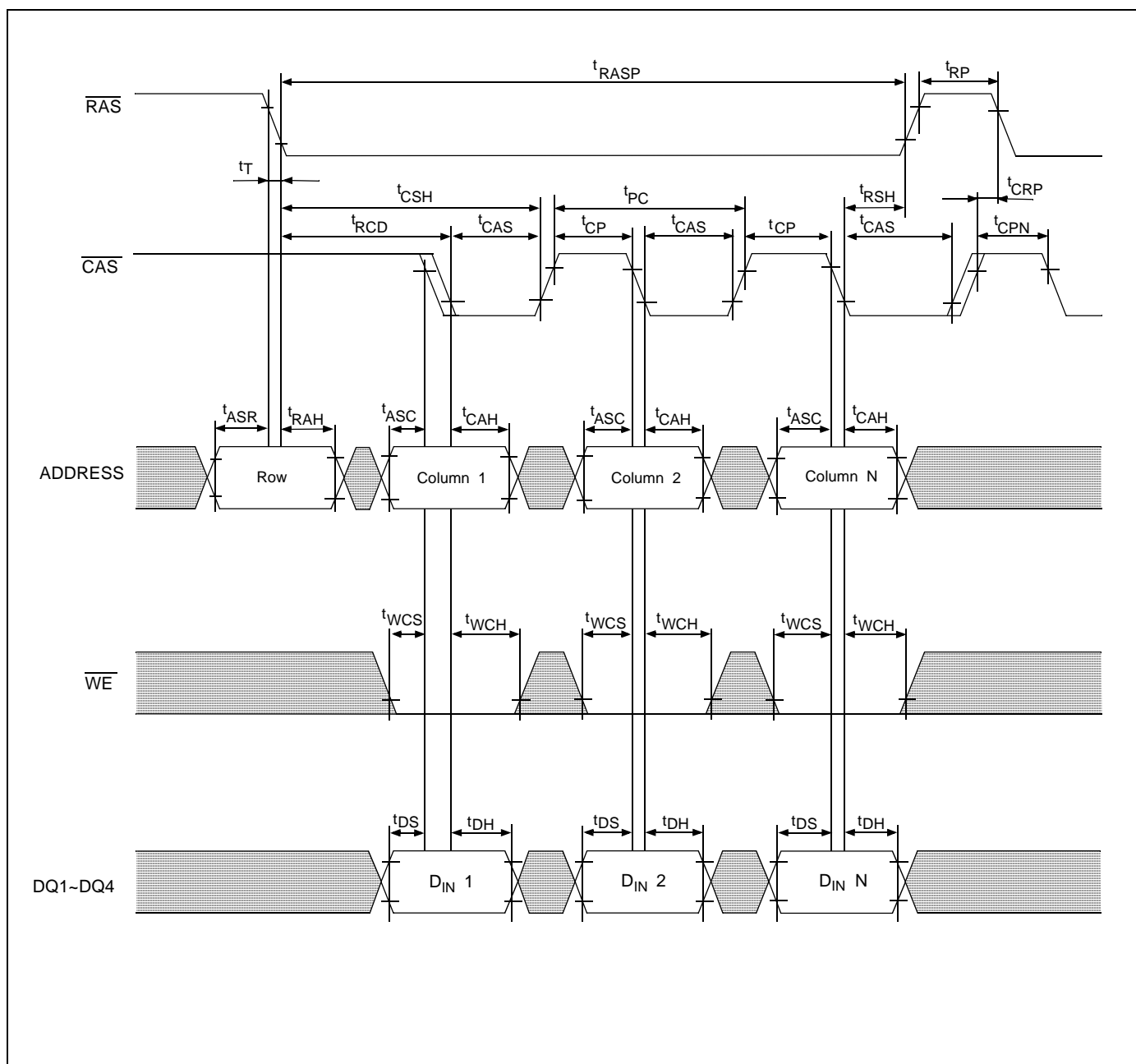


[illegible]

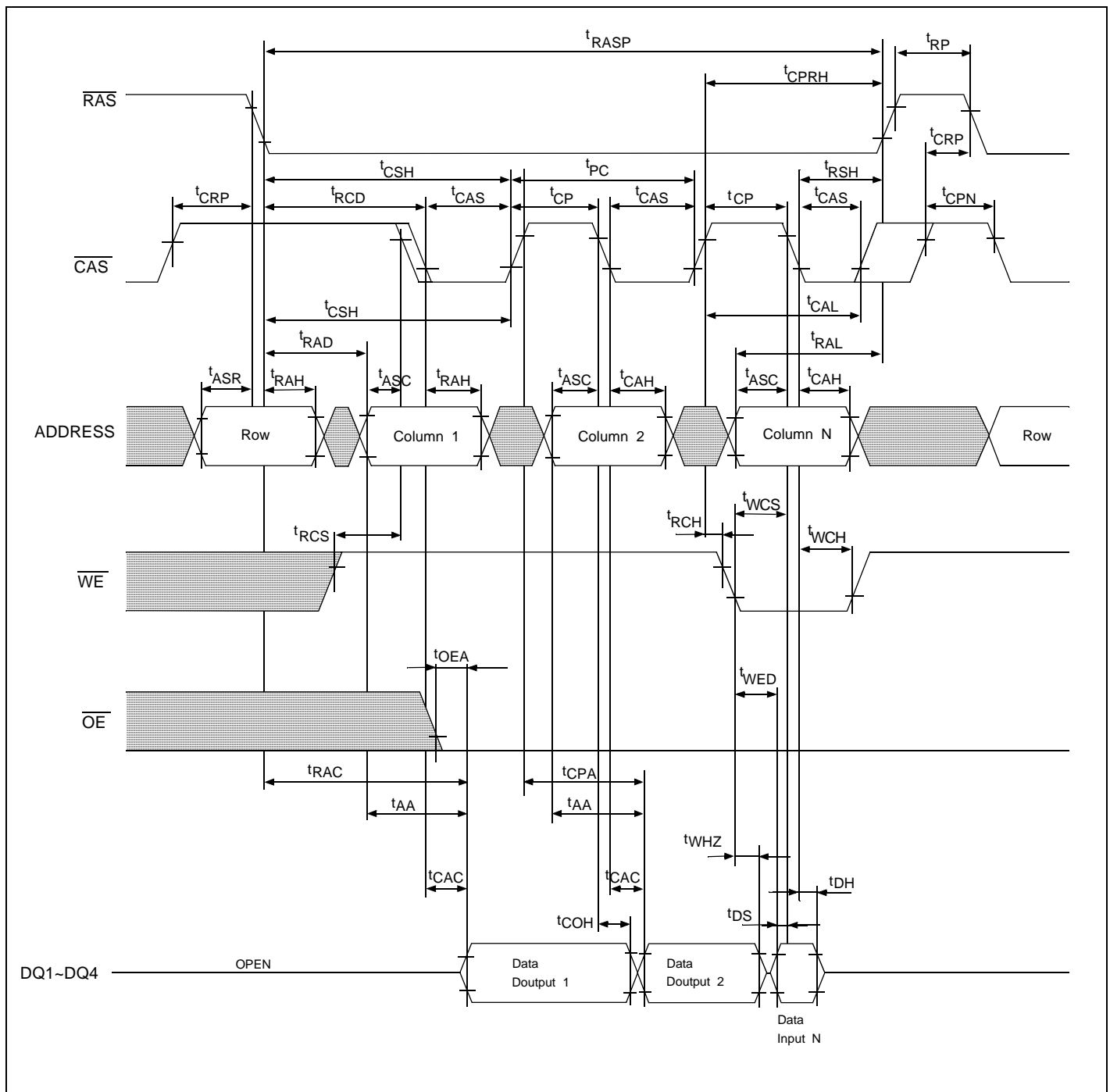
The diagram illustrates the timing relationships for a memory device. The signals shown are $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, ADDRESS, $\overline{\text{WE}}$, $\overline{\text{OE}}$, and DQ1-DQ4. The timing parameters are defined as follows:

- t_{RASP} : RAS pulse width
- t_{CRP} : RAS to CAS setup time
- t_{CSH} : CAS setup time
- t_{PC} : CAS to RAS period
- t_{RSH} : RAS hold time
- t_{CPN} : CAS to RAS period
- t_{RAD} : RAS to data access time
- t_{ASC} : Address to data access time
- t_{CAH} : Column address hold time
- t_{RCS} : RAS to column address setup time
- t_{RRH} : RAS to row address hold time
- t_{RCH} : RAS to row address hold time
- t_{OEHC} : Output enable high to data access time
- t_{OEP} : Output enable pulse width
- t_{OEZ} : Output enable to data access time
- t_{OFF} : Output enable to data access time
- t_{RAC} : RAS to data access time
- t_{AA} : Address to data access time
- t_{CAC} : Column address to data access time
- t_{COH} : Column address hold time
- t_{DOUT} : Data output time
- t_{OPEN} : Data output open time

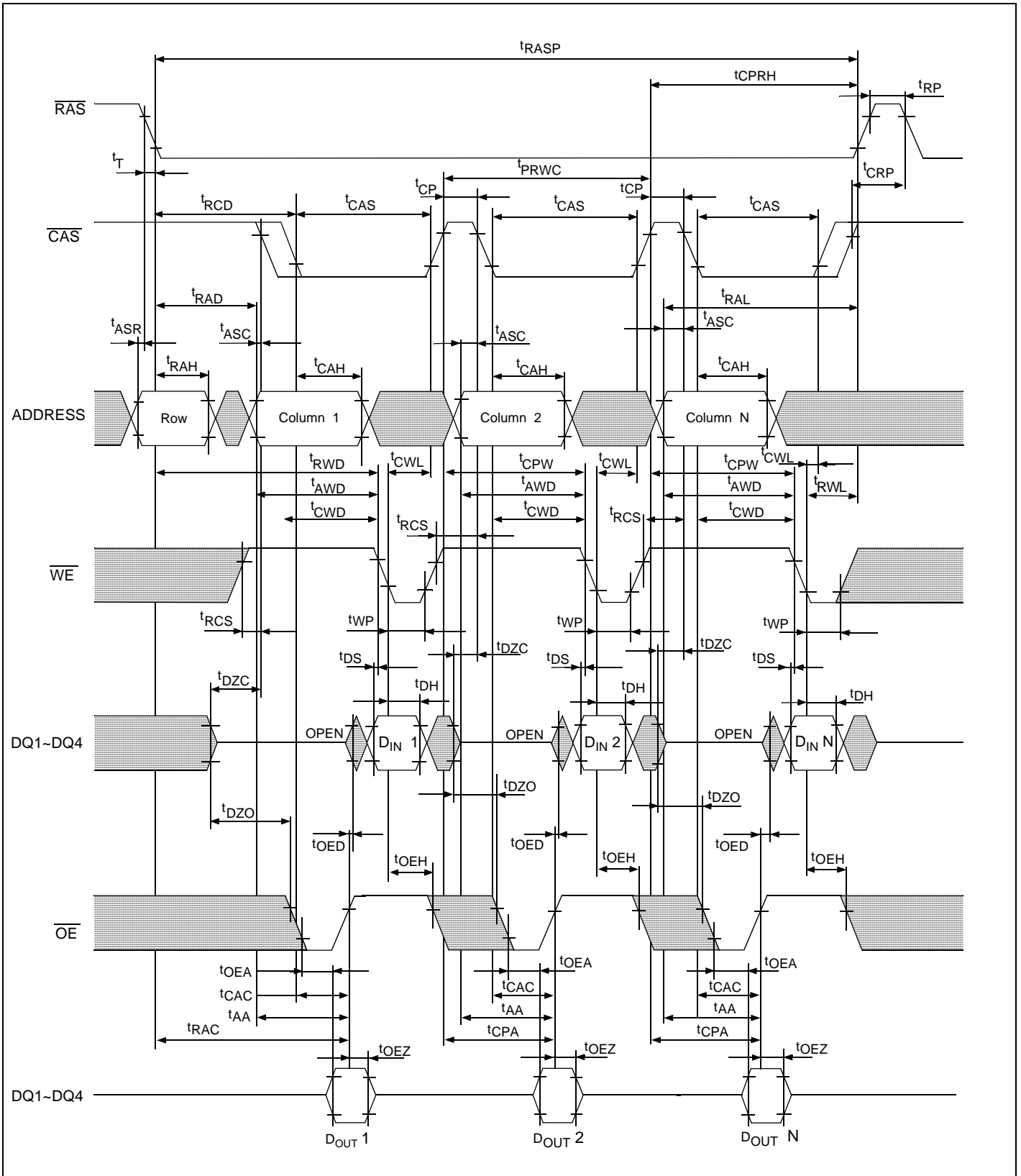
• EDO Page Mode Early Write Cycle



- EDO Page Mode Read-Early-Write Cycle



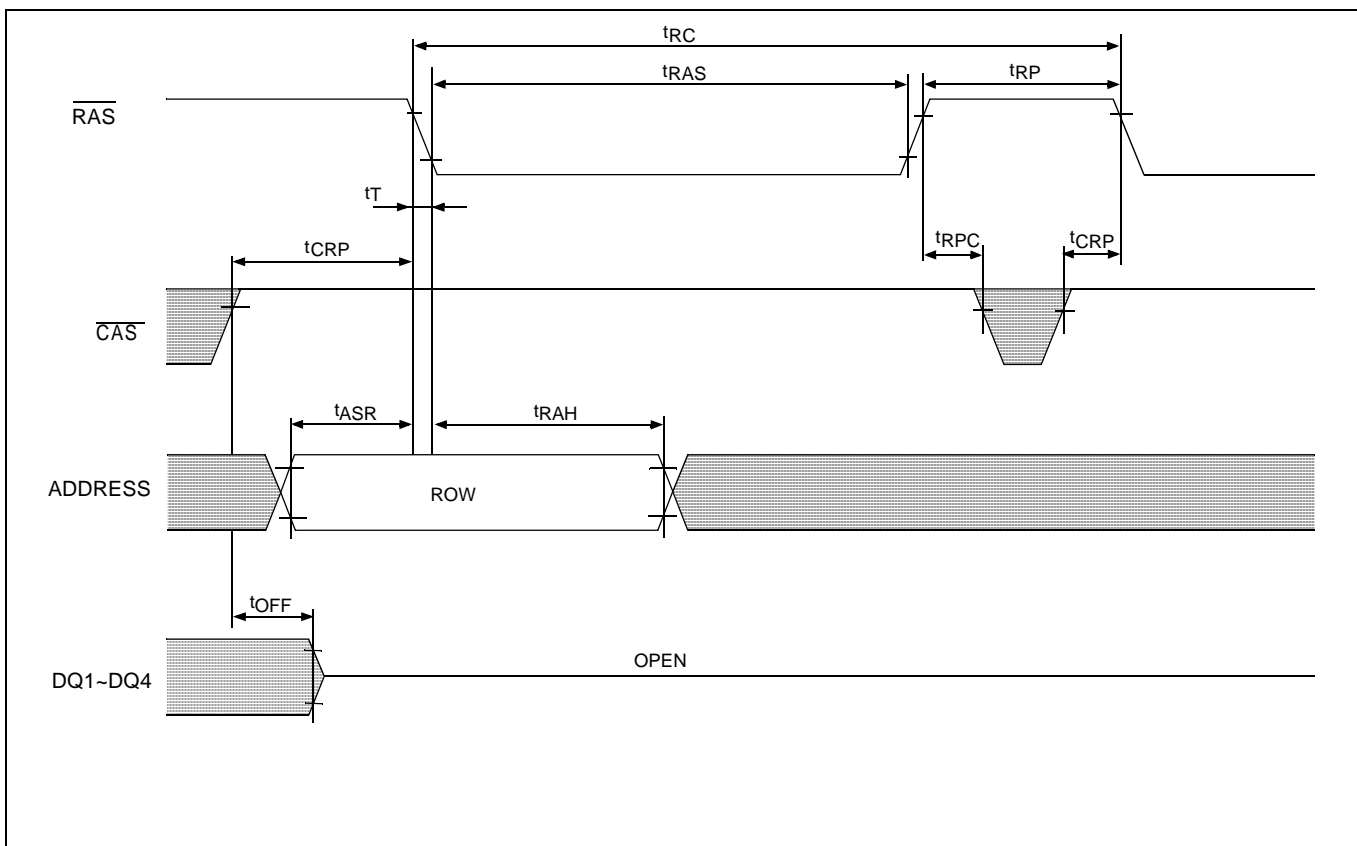
• EDO Page Mode Read-Modify-Write Cycle



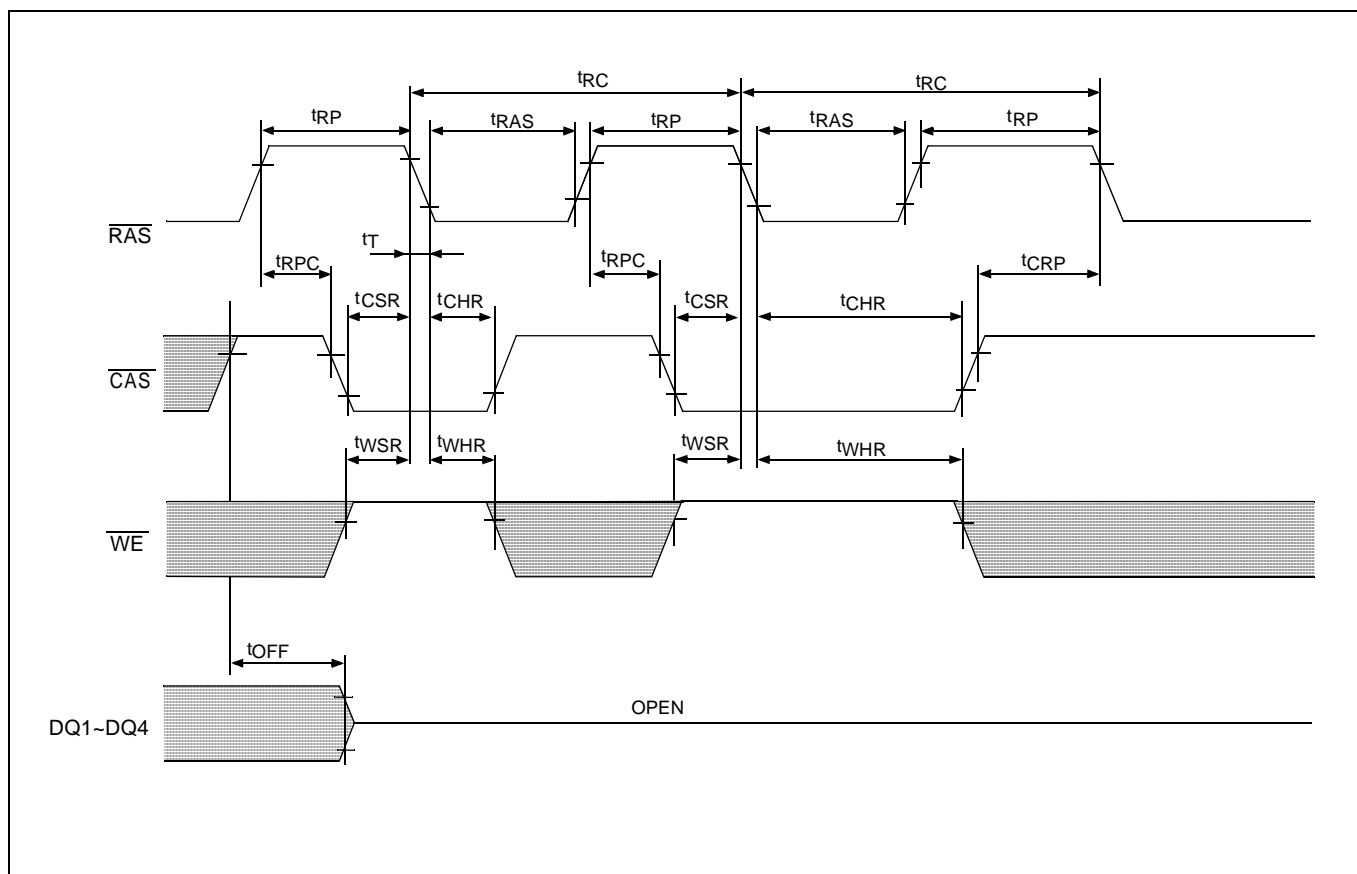
The diagram illustrates the timing relationships for a memory device. The signals and their timing parameters are as follows:

- RAS**: Row Address Strobe. Timing parameters include t_{CSH} (RAS to CAS setup), t_{RCD} (RAS to CAS delay), and t_{RAD} (RAS to data output delay).
- CAS**: Column Address Strobe. Timing parameters include t_{CAS} (CAS to data output delay), t_{ASC} (CAS to data output delay), and t_{CAH} (CAS to data output delay).
- ADDRESS**: Memory address. Timing parameters include t_{ASR} (ADDRESS to RAS setup), t_{RAH} (ADDRESS to RAS hold), t_{ASC} (ADDRESS to CAS setup), and t_{CAH} (ADDRESS to CAS hold).
- WE**: Write Enable. Timing parameters include t_{RCS} (RAS to WE setup), t_{RCH} (RAS to WE hold), t_{WPZ} (WE pulse width), and t_{WHZ} (WE hold).
- OE**: Output Enable. Timing parameters include t_{OEA} (OE to data output delay), t_{CAC} (OE to data output delay), t_{OEZ} (OE to data output delay), t_{AA} (OE to data output delay), and t_{RAC} (OE to data output delay).
- DQ1~DQ4**: Data bus. Timing parameters include t_{CLZ} (data output delay) and D_{OUT} (data output).

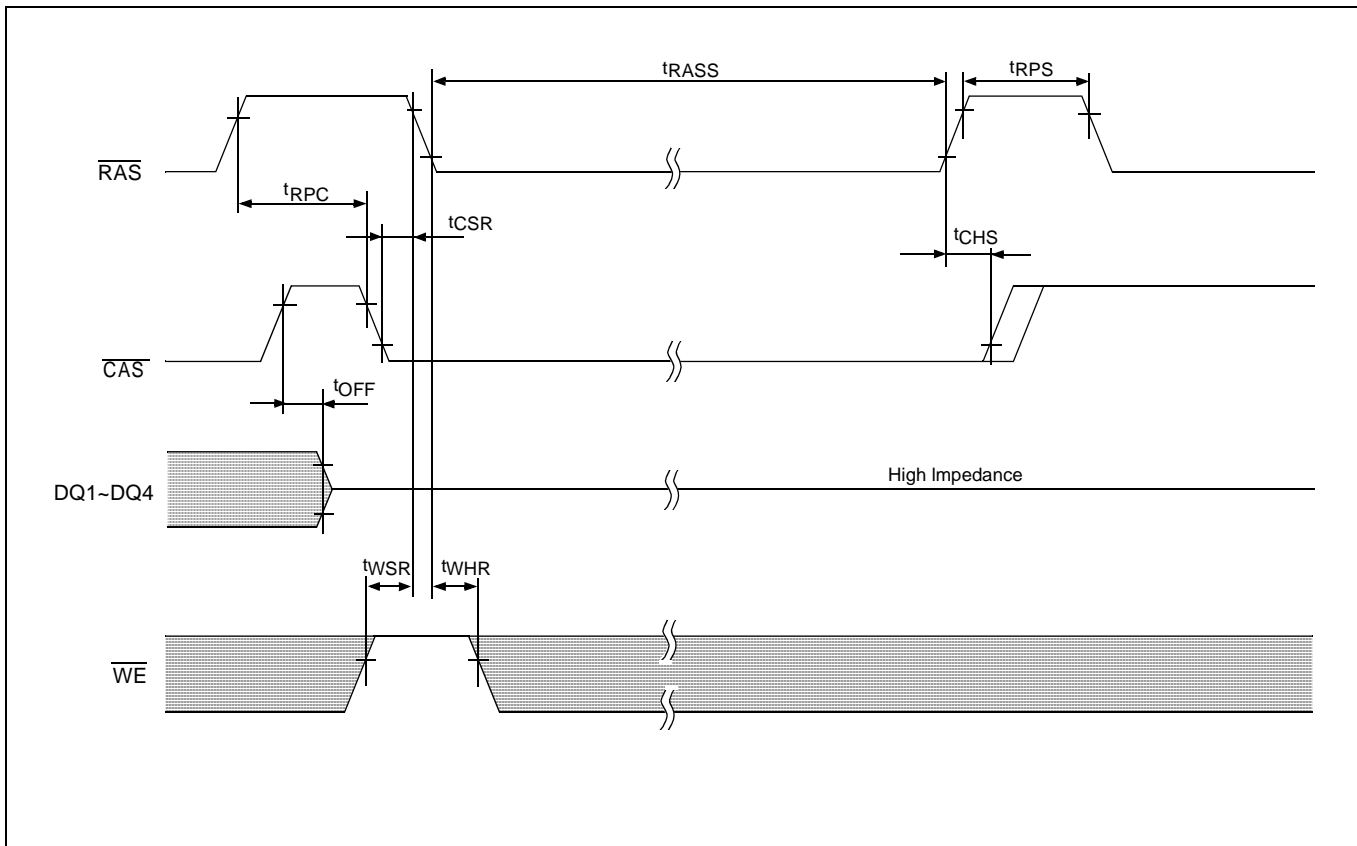
RAS-Only Refresh Cycle



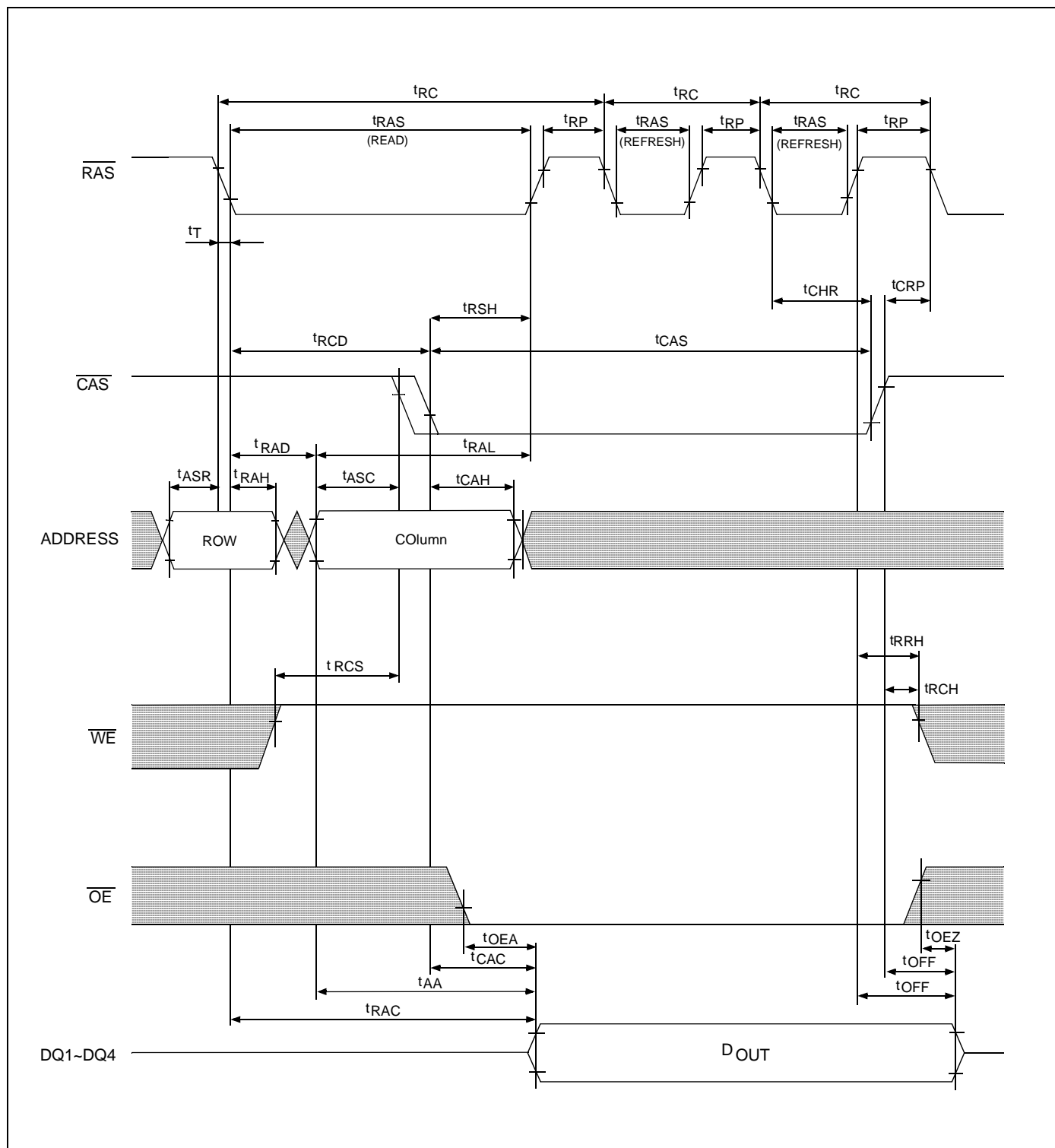
CAS-Before-RAS Refresh Cycle



CBR Self-Refresh Cycle



• Hidden Refresh Cycle



Ordering information

Part Number	Access time	Package
VG26(V)(S)17405FJ(L)-5	50 ns	300mil 26/24-Pin
VG26(V)(S)17405FJ(L)-6	60 ns	Plastic SOJ
VG26(V)(S)17405FT(L)-5	50 ns	300mil 26/24-Pin
VG26(V)(S)17405FT(L)-6	60 ns	TSOP II

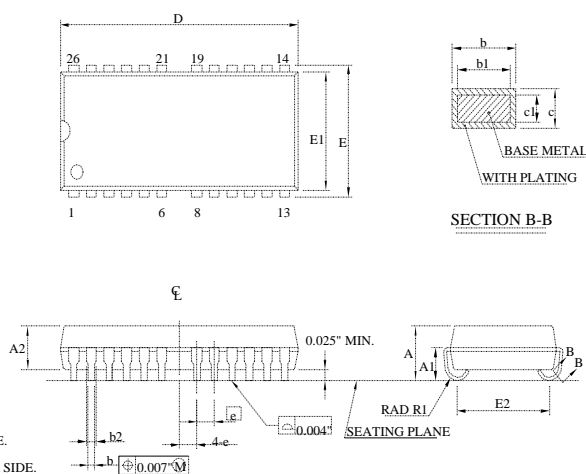
VG26(V)(S) 17405FJ-5

- VG → • VIS Memory Product
- 26 → • Technology
- V → • 3.3V Version
- S → • Self refresh
- 17405 → • Device Type and Configuration
- F → • Revision
- J → • Package Type (J : SOJ, T : TSOP II)
- L → • None: normal version, L: low power version
- 5 → • Speed (5 : 50 ns, 6 : 60 ns)

Packaging information

- 300 mil, 26/24-Pin Plastic SOJ

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	3.25	3.51	3.76	0.128	0.138	0.148
A1	2.08	---	---	0.082	---	---
A2	2.54 REF.			0.100 REF.		
b	0.41	---	0.51	0.016	---	0.020
b1	0.41	0.46	0.48	0.016	0.018	0.019
b2	0.66	---	0.81	0.026	---	0.032
c	0.18	---	0.30	0.007	---	0.012
c1	0.18	---	0.28	0.007	---	0.011
D	17.02	17.15	17.27	0.670	0.675	0.680
E	8.51 BASIC			0.335 BASIC		
E1	7.49	7.62	7.75	0.295	0.300	0.305
E2	6.78 BASIC			0.267 BASIC		
e	1.27 BASIC			0.050 BASIC		
F1	0.76	---	1.02	0.030	---	0.040



NOTE:

- NOTE:
1. CONTROLLING DIMENSION : INCHES
 2. DIMENSION D DOES NOT INCLUDE MOLD PROTRUSION.
MOLD PROTRUSION SHALL NOT EXCEED $0.006'' (0.15\text{mm})$ PER SIDE.
DIMENSION E1 DOES NOT INCLUDE INTERLEAF PROTRUSION.
INTERLEAF PROTRUSION SHALL NOT EXCEED $0.01'' (0.25\text{mm})$ PER SIDE.
 3. DIMENSION B2 DOES NOT INCLUDE DAMBAR PROTRUSION OR INTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE SHOULDER WIDTH TO EXCEED 2 MILS BY MORE THAN $0.005'' (0.127\text{mm})$.
DAMBAR INTRUSION SHALL NOT REDUCE THE SHOULDER WIDTH TO LESS THAN $0.001'' (0.025\text{mm})$ BELOW 2 MILS .

• 300 mil, 26/24-Pin TSOP II

